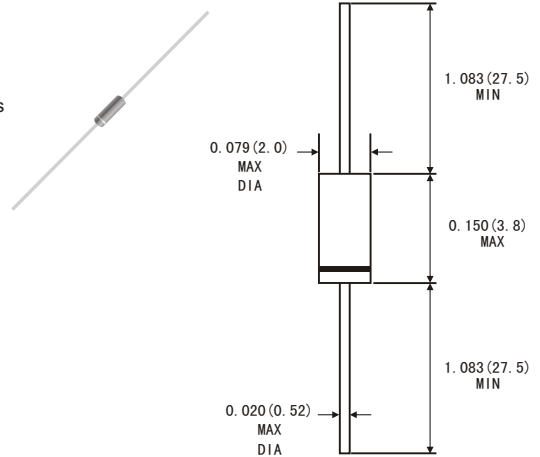


FEATURES

- Metal-on-silicon junction
 - Low turn-on voltage
 - Ultrafast switching speed
 - Primarily intended for high level UHF mixers and ultrafast switching applications
- The diode is also available in the MiniMELF case with type designation LL29.
- High temperature soldering guaranteed: 260°C / 10 seconds at terminals
 - Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC

DO-35



Dimensions in inches and (millimeters)

MECHANICAL DATA

- Case: DO-35 glass case
- *Polarity*: color band denotes cathode end
- *Weight*: Approx. 0.13 gram

ABSOLUTE RATINGS(LIMITING VALUES)

	Symbols	Value	Units
Peak Reverse Voltage	V _{RRM}	5	V
Forward Continuous Current	I _F	30	mA
Surge non repetitive forward current $t_p \leq 1s$	I _{FSM}	60	mA
Junction and Storage temperature range	T _{STG}	-65 to +150	°C
	T _J	-65 to +150	°C
Maximum Lead Temperature for Soldering during 10s at 4mm from Case	T _L	230	°C

ELECTRICAL CHARACTERISTICS

	Symbols	Min.	Typ.	Max.	Units
Reverse breakover voltage at I _R =100μA	V _R	5			V
Leakage current at V _R =1V	I _R			50	nA
Forward voltage drop at I _F =10mA Test pulse: $t_p \leq 300\mu s$ $\delta < 2\%$	V _F			0.55	V
Junction Capacitance at V _R =0V, f=1GHz	C _J			1.0	pF
Thermal resistance	R _{θJA}			400	K/W



Figure 1. forward current versus forward voltage (typical values)

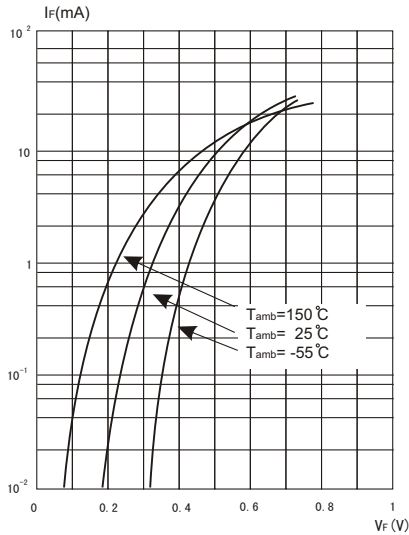


Figure 2. Capacitance C_j versus reverse applied voltage V_R (typical values)

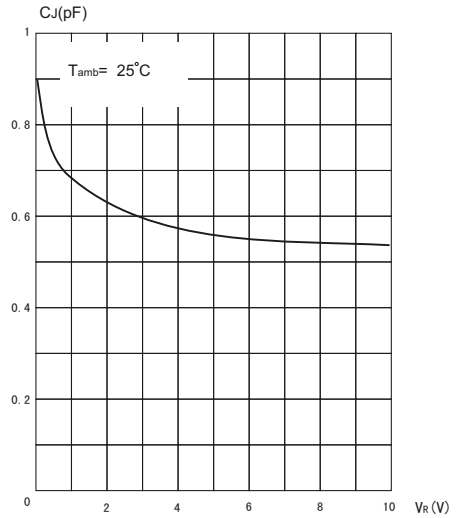


Figure 3. Reverse current versus ambient temperature

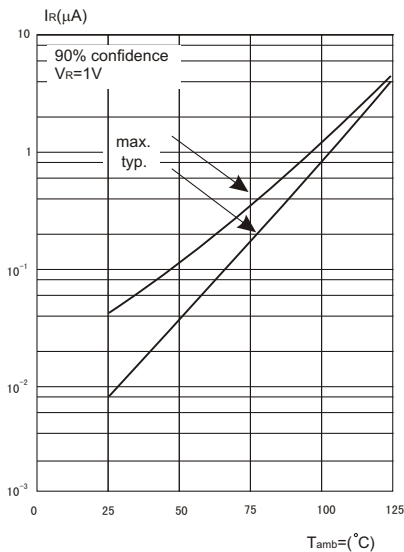


Figure 4. Reverse current versus continuous Reverse voltage (typical values)

